STH12N120K5-2, STP12N120K5, STW12N120K5, STWA12N120K5

N-channel 1200 V, 0.62 Ω typ.,12 A MDmesh K5 Power MOSFETs in H²PAK-2, TO-220, TO-247 and TO-247 long leads

Datasheet - production data

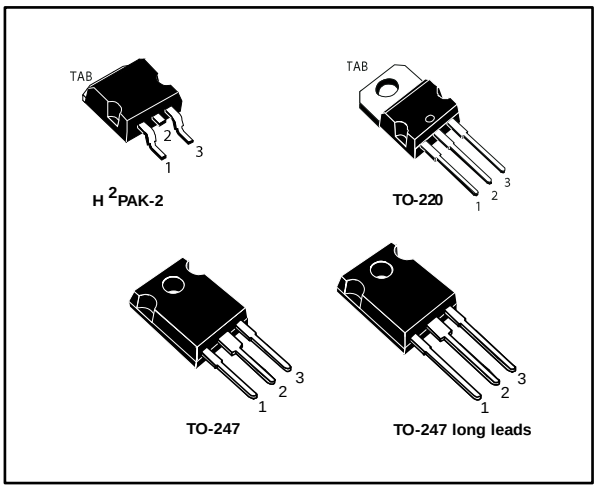
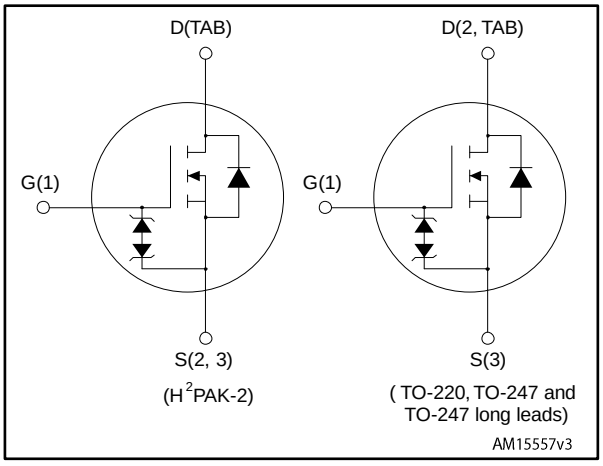


Figure 1: Internal schematic diagram



Features

Order codes	V_{DS}	$R_{DS(on)}$ max.	I_D	P_{TOT}
STH12N120K5-2	1200 V	0.69 Ω	12 A	250 W
STP12N120K5				
STW12N120K5				
STWA12N120K5				

- Worldwide best FOM (figure of merit)
- Ultra-low gate charge
- 100% avalanche tested
- Zener-protected

Applications

- Switching applications

Description

These very high voltage N-channel Power MOSFETs are designed using MDmesh™ K5 technology based on an innovative proprietary vertical structure. The result is a dramatic reduction in on-resistance and ultra-low gate charge for applications requiring superior power density and high efficiency.

Table 1: Device summary

Order code	Marking	Package	Packing
STH12N120K5-2	12N120K5	H²PAK-2	Tape and reel
STP12N120K5		TO-220	Tube
STW12N120K5		TO-247	
STWA12N120K5		TO-247 long leads	

Contents

1 Electrical ratings

Table 2: Absolute maximum ratings

Symbol	Parameter	Value	Unit
V_{GS}	Gate-source voltage	± 30	V
I_D	Drain current at T_C = 25 °C	12	A
I_D	Drain current at T_C = 100 °C	7.6	A
I_{DM} (1)	Drain current (pulsed)	48	A
P_{TOT}	Total dissipation at T_C = 25 °C	250	W
I_{AR} (2)	Max current during repetitive or single pulse avalanche	4	A
E_{AS} (3)	Single pulse avalanche energy	215	mJ
dv/dt (4)	Peak diode recovery voltage slope	4.5	V/ns
dv/dt (5)	MOSFET dv/dt ruggedness	50	V/ns
T_j T_{stg}	Operating junction temperature Storage temperature	- 55 to 150	°C

Notes:

(1)Pulse width limited by safe operating area.

(2)Pulse width limited by $T_{Jmax.}$

(3)Starting T_J = 25 °C, I_D=I_{AS}, V_{DD}= 50 V

(4)I_{SD} ≤ 12 A, di/dt ≤ 100 A/µs, V_{Peak} ≤ $V_{(BR)DSS}$

(5)V_{DS} ≤ 960 V

Table 3: Thermal data

Symbol	Parameter	Value			Unit
		H^2PAK-2	TO-220	TO-247 TO-247 long leads	
$R_{thj\text{-}case}$	Thermal resistance junction-case max	0.5			°C/W
$R_{thj\text{-}amb}$	Thermal resistance junction-amb max		62.5	50	°C/W
$R_{thj\text{-}pcb}$	Thermal resistance junction-pcb max	30			°C/W

2 Electrical characteristics

(T_{CASE} = 25 °C unless otherwise specified)

Table 4: On/off states

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$V_{(BR)DSS}$	Drain-source breakdown voltage	V_{GS} = 0 V, I_D = 1 mA	1200			V
I_{DSS}	Zero gate voltage drain current	V_{GS} = 0 V, V_{DS} = 1200 V			1	µA
		V_{GS} = 0, V_{DS} = 1200 V, Tc = 125 °C			50	µA
I_{GSS}	Gate body leakage current	V_{DS} = 0 V, V_{GS} = ± 20 V			±10	µA
$V_{GS(th)}$	Gate threshold voltage	V_{DS} = V_{GS}, I_D = 100 µA	3	4	5	V
$R_{DS(on)}$	Static drain-source on-resistance	V_{GS} = 10 V, I_D= 6 A		0.62	0.69	Ω

Table 5: Dynamic

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
C_{iss}	Input capacitance	V_{GS} = 0 V, V_{DS} = 100 V, f = 1 MHz	-	1370	-	pF
C_{oss}	Output capacitance		-	110	-	pF
C_{rss}	Reverse transfer capacitance		-	0.6	-	pF
$C_{o(tr)}$ (1)	Equivalent capacitance, time-related	V_{GS} = 0, V_{DS} = 0 to 960 V	-	128	-	pF
$C_{o(er)}$ (2)	Equivalent capacitance, energy-related		-	42	-	pF
R_G	Intrinsic gate resistance	f = 1 MHz, I_D = 0 A	-	3	-	Ω
Q_g	Total gate charge	V_{DD} = 960 V, I_D = 12 A V_{GS} = 10 V (see *Figure 18: "Gate charge test circuit"*)	-	44.2	-	nC
Q_{gs}	Gate-source charge		-	7.3	-	nC
Q_{gd}	Gate-drain charge		-	30	-	nC

Notes:

(1)Time-related is defined as a constant equivalent capacitance giving the same charging time as C_{oss} when V_{DS} increases from 0 to 80% V_{DSS}

(2)Energy-related is defined as a constant equivalent capacitance giving the same stored energy as C_{oss} when V_{DS} increases from 0 to 80% V_{DSS}

Table 6: Switching times

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$t_{d(on)}$	Turn-on delay time	V_{DD} = 600 V, I_D = 6 A, R_G = 4.7 Ω, V_{GS} = 10 V (see *Figure 20: "Unclamped inductive load test circuit"*)	-	23	-	ns
t_r	Rise time		-	11	-	ns
$t_{d(off)}$	Turn-off delay time		-	68.5	-	ns
t_f	Fall time		-	18.5	-	ns

Table 7: Source drain diode

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
I_{SD}	Source-drain current		-		12	A
I_{SDM}	Source-drain current (pulsed)		-		48	A
V_{SD} (1)	Forward on voltage	I_{SD} = 12 A, V_{GS} = 0 V	-		1.5	V
t_{rr}	Reverse recovery time	I_{SD} = 12 A, V_{DD} = 60 V di/dt = 100 A/µs, (see *Figure 19: "Test circuit for inductive load switching and diode recovery times"*)	-	630		ns
Q_{rr}	Reverse recovery charge		-	12.6		µC
I_{RRM}	Reverse recovery current		-	40		A
t_{rr}	Reverse recovery time	I_{SD} = 12 A,V_{DD} = 60 V di/dt = 100 A/µs, Tj = 150 °C (see *Figure 19: "Test circuit for inductive load switching and diode recovery times"*)	-	892		ns
Q_{rr}	Reverse recovery charge		-	15.6		µC
I_{RRM}	Reverse recovery current		-	35		A

Notes:

(1)Pulsed: pulse duration = 300µs, duty cycle 1.5%

Table 8: Gate-source Zener diode

Symbol	Parameter	Test conditions	Min	Typ.	Max.	Unit
$V_{(BR)GSO}$	Gate-source breakdown voltage	I_{GS} = ±1 mA, I_D = 0 A	30	-		V

The built-in back-to-back Zener diodes have been specifically designed to enhance the ESD capability of the device. The Zener voltage is appropriate for efficient and cost-effective intervention to protect the device integrity. These integrated Zener diodes thus eliminate the need for external components.

2.1 Electrical characteristics (curves)

Figure 2: Safe operating area for H²PAK-2 and TO-220

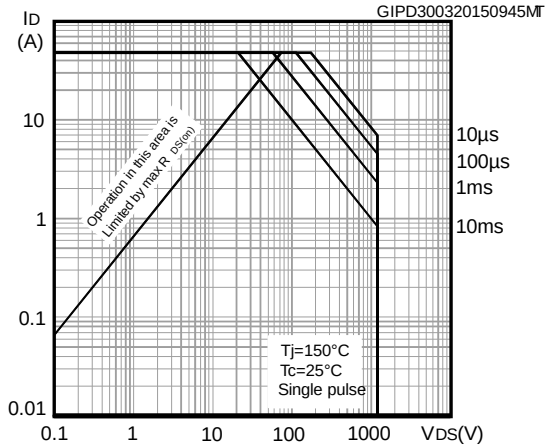


Figure 3: Thermal impedance for H²PAK-2 and TO-220

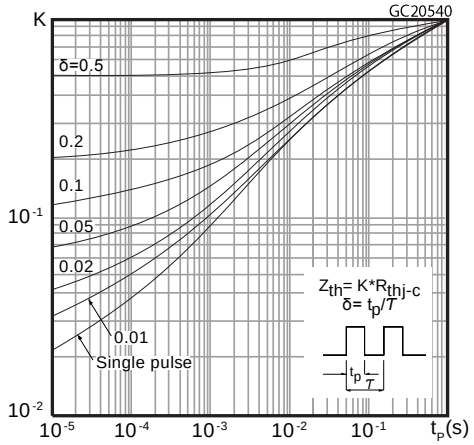


Figure 4: Safe operating area for TO-247 and TO-247 long leads

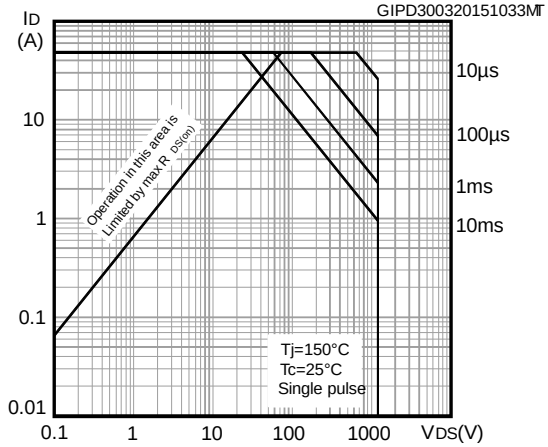


Figure 5: Thermal impedance for TO-247 and TO-247 long leads

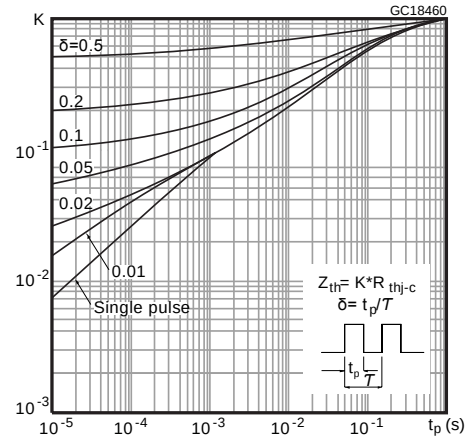


Figure 6: Output characteristics

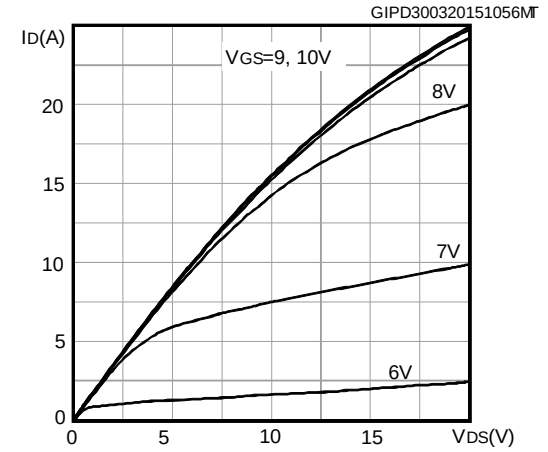


Figure 7: Transfer characteristics

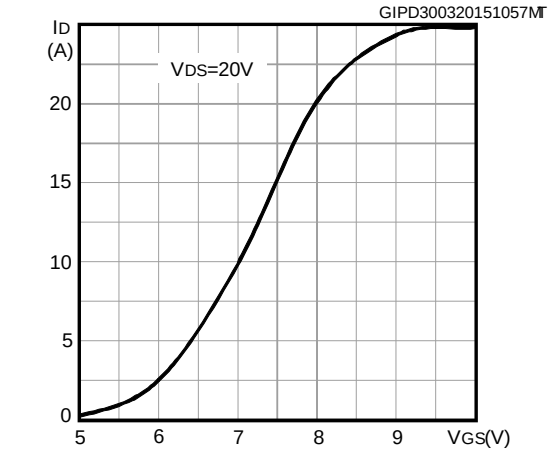


Figure 8: Gate charge vs gate-source voltage

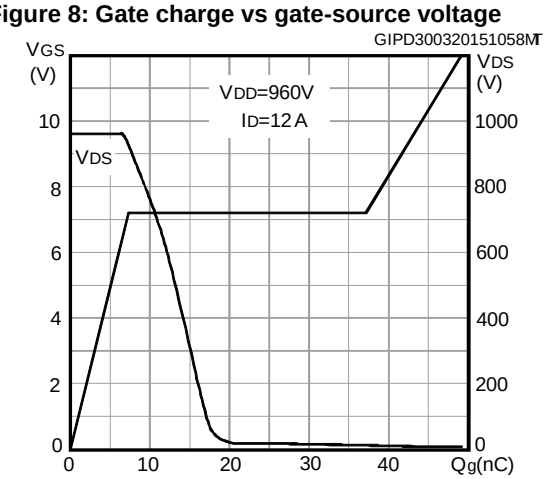


Figure 9: Static drain-source on-resistance

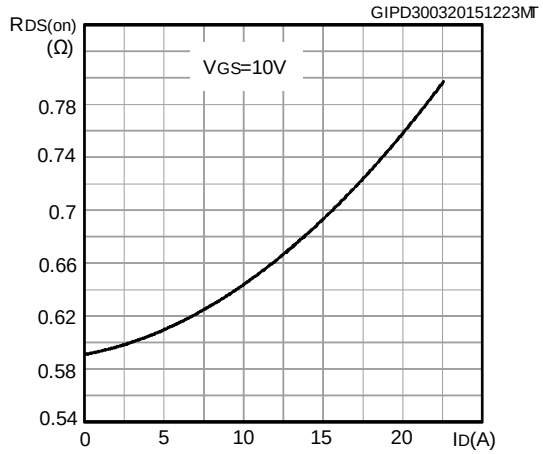


Figure 10: Capacitance variations

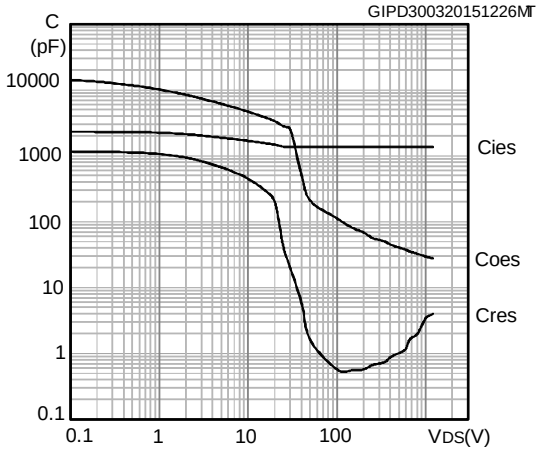


Figure 11: Output capacitance stored energy

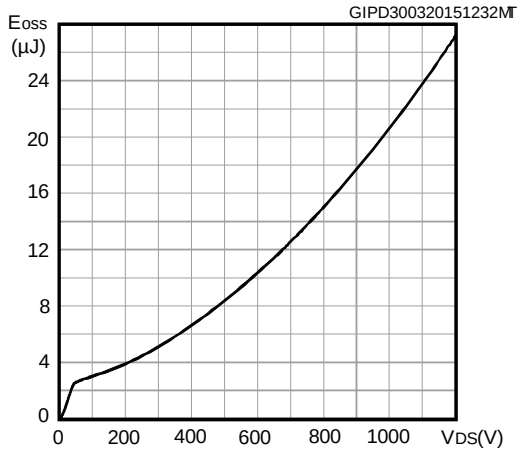


Figure 12: Normalized gate threshold voltage vs temperature

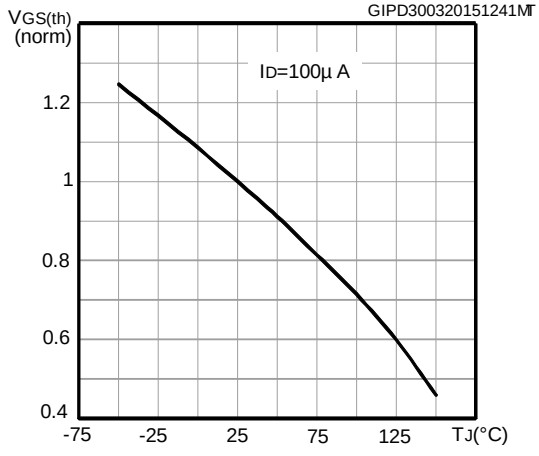


Figure 13: Normalized on-resistance vs temperature

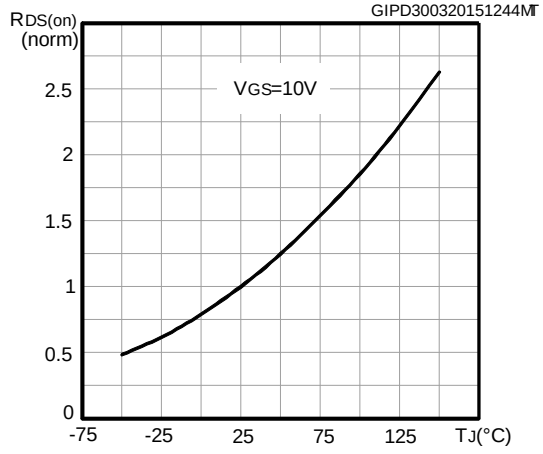


Figure 14: Normalized $V_{(BR)DSS}$ vs temperature

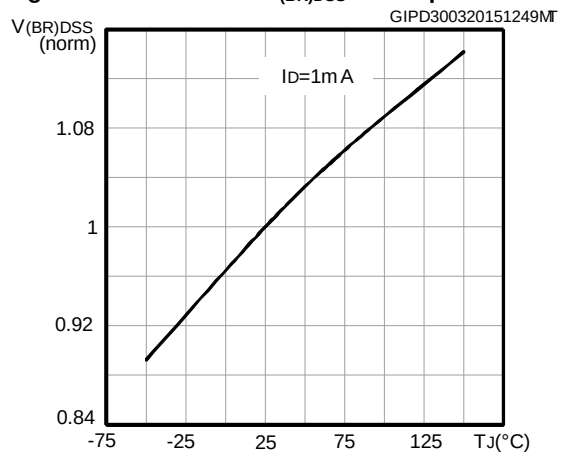


Figure 15: Source-drain diode forward characteristics

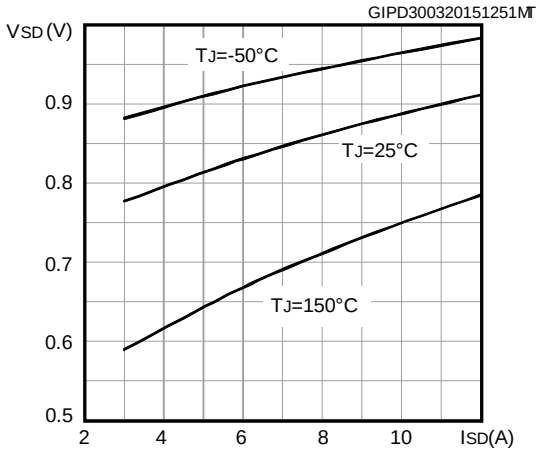
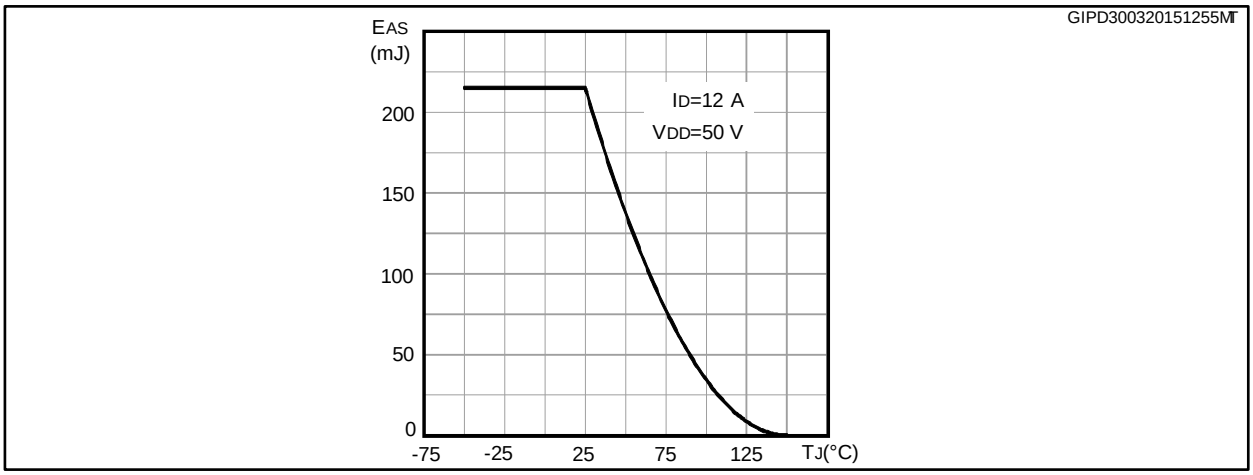


Figure 16: Maximum avalanche energy vs starting T_J



3 Test circuits

Figure 17: Switching times test circuit for resistive load

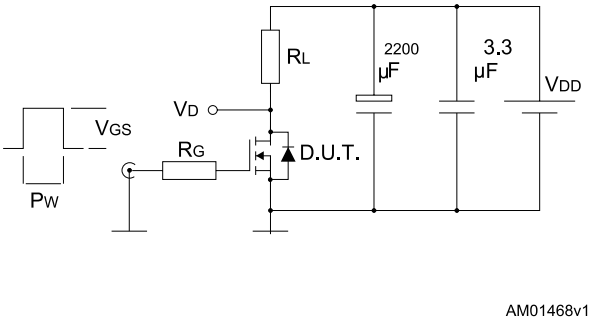


Figure 18: Gate charge test circuit

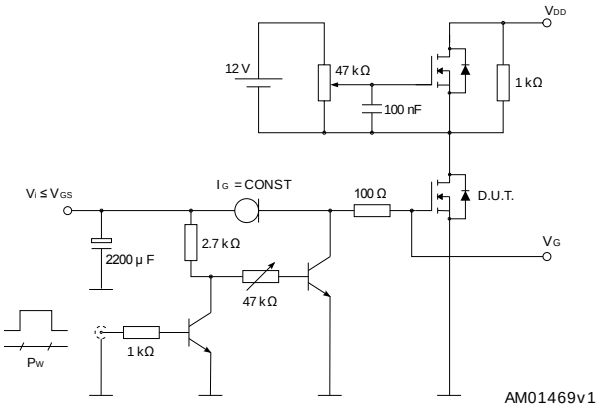


Figure 19: Test circuit for inductive load switching and diode recovery times

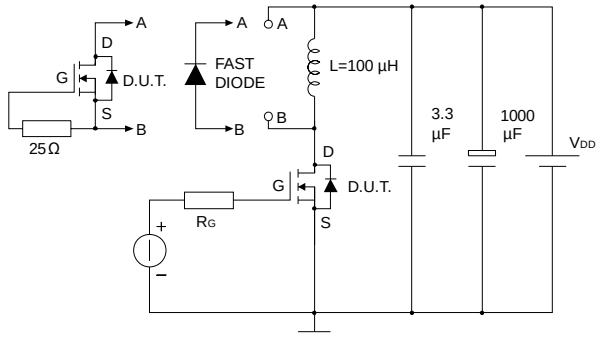


Figure 20: Unclamped inductive load test circuit

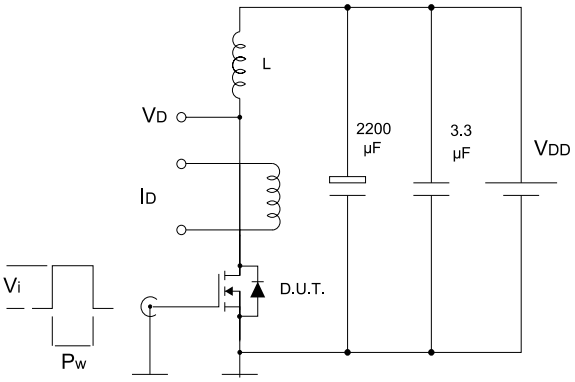


Figure 21: Unclamped inductive waveform

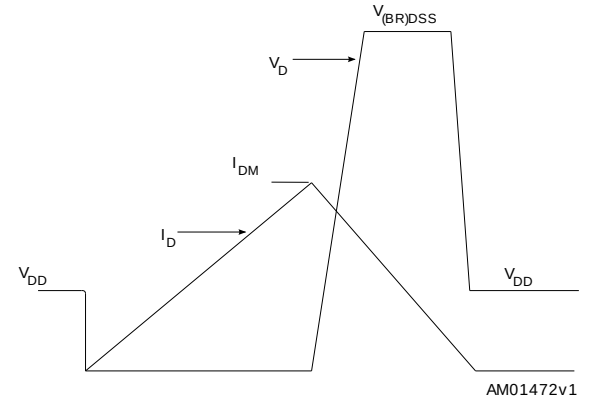
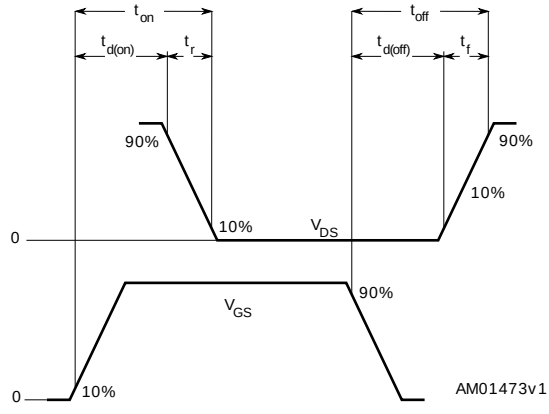


Figure 22: Switching time waveform



4 Package information

In order to meet environmental requirements, ST offers these devices in different grades of ECOPACK® packages, depending on their level of environmental compliance. ECOPACK® specifications, grade definitions and product status are available at: ***www.st.com***. ECOPACK® is an ST trademark.

4.1 H²PAK-2 package information

Figure 23: H²PAK-2 package outline

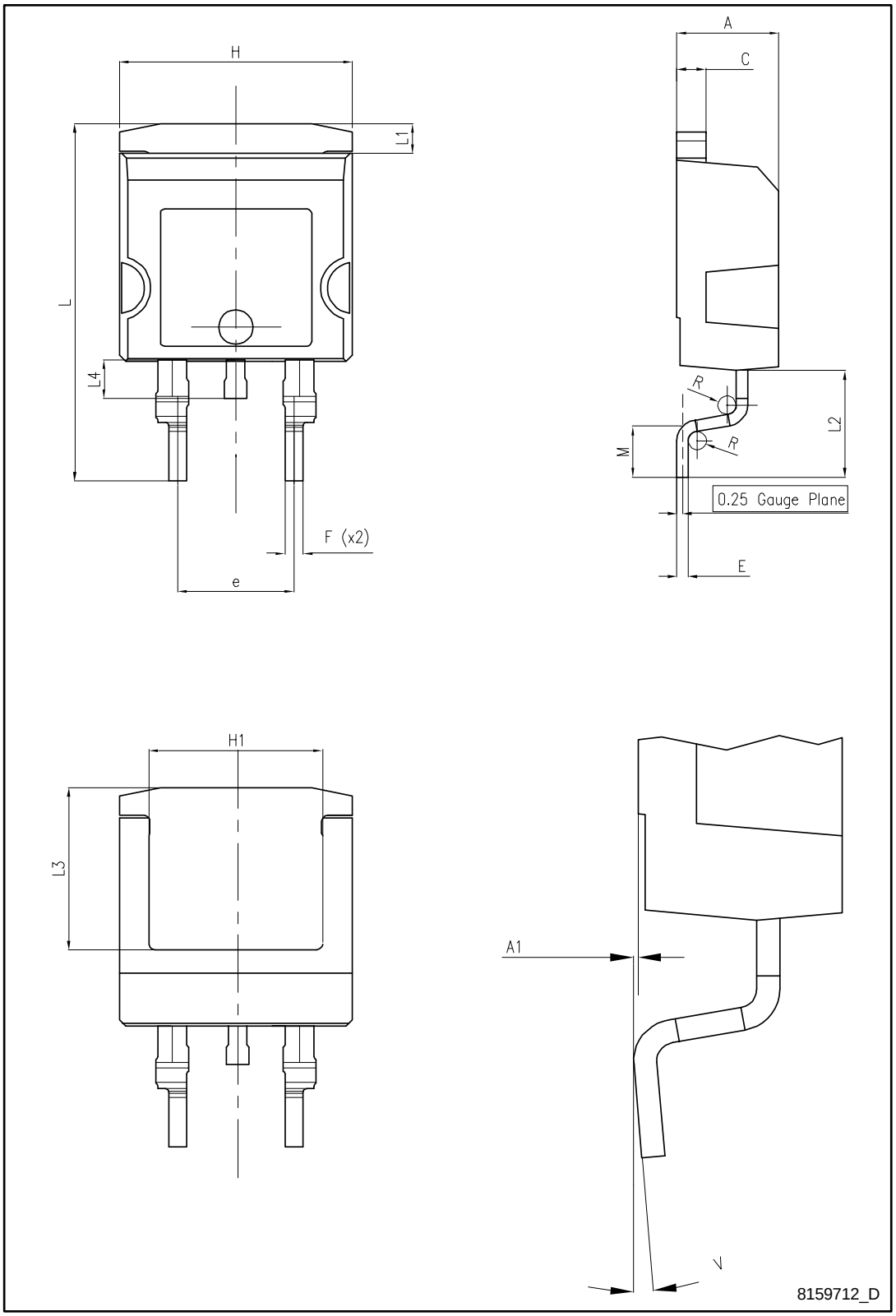
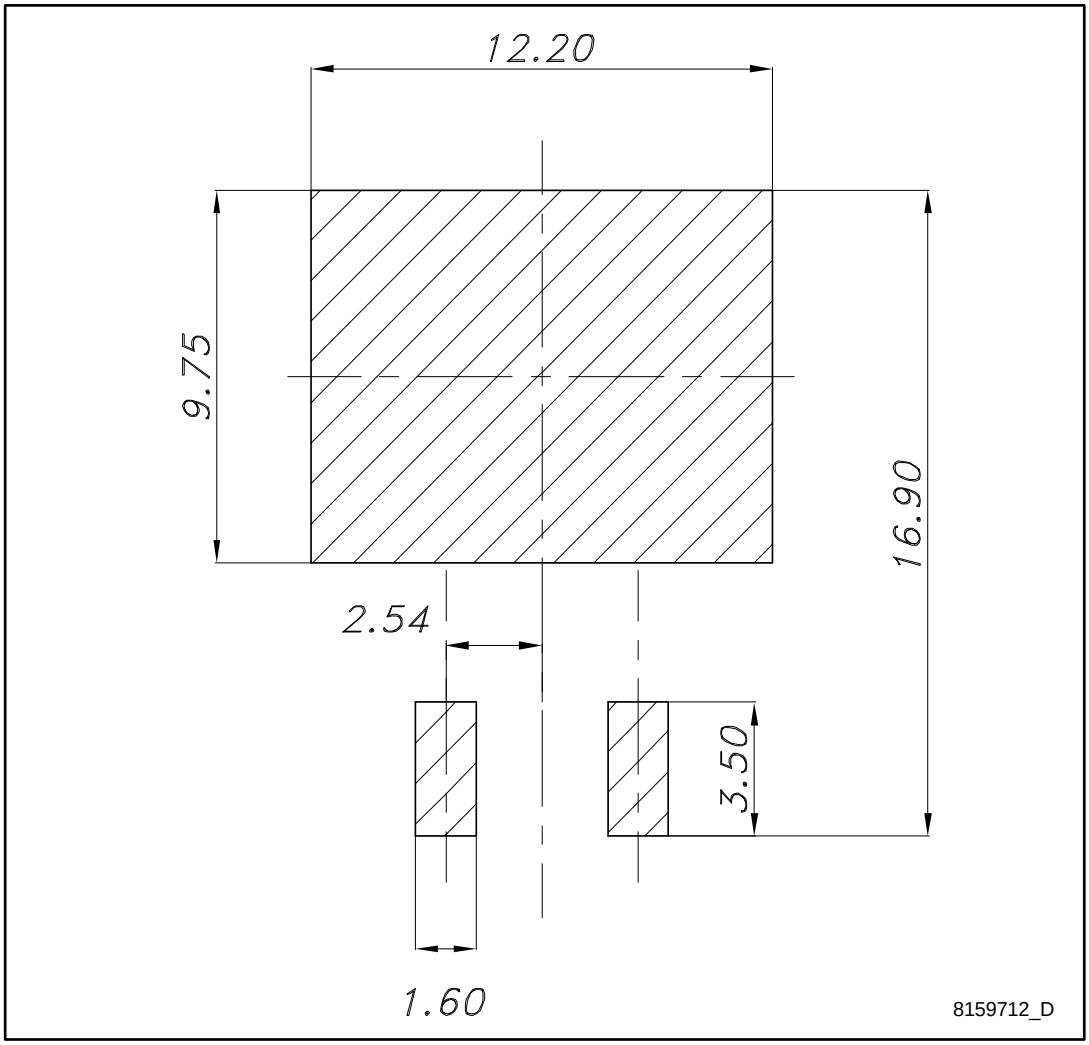


Table 9: H²PAK-2 mechanical data

Dim.	mm		
	Min.	Typ.	Max.
A	4.30	-	4.80
A1	0.03		0.20
C	1.17		1.37
e	4.98		5.18
E	0.50		0.90
F	0.78		0.85
H	10.00		10.40
H1	7.40		7.80
L	15.30		15.80
L1	1.27		1.40
L2	4.93		5.23
L3	6.85		7.25
L4	1.5		1.7
M	2.6		2.9
R	0.20		0.60
V	0°		8°

Figure 24: H²PAK-2 recommended footprint



4.2 TO-220 type A package information

Figure 25: TO-220 type A package outline

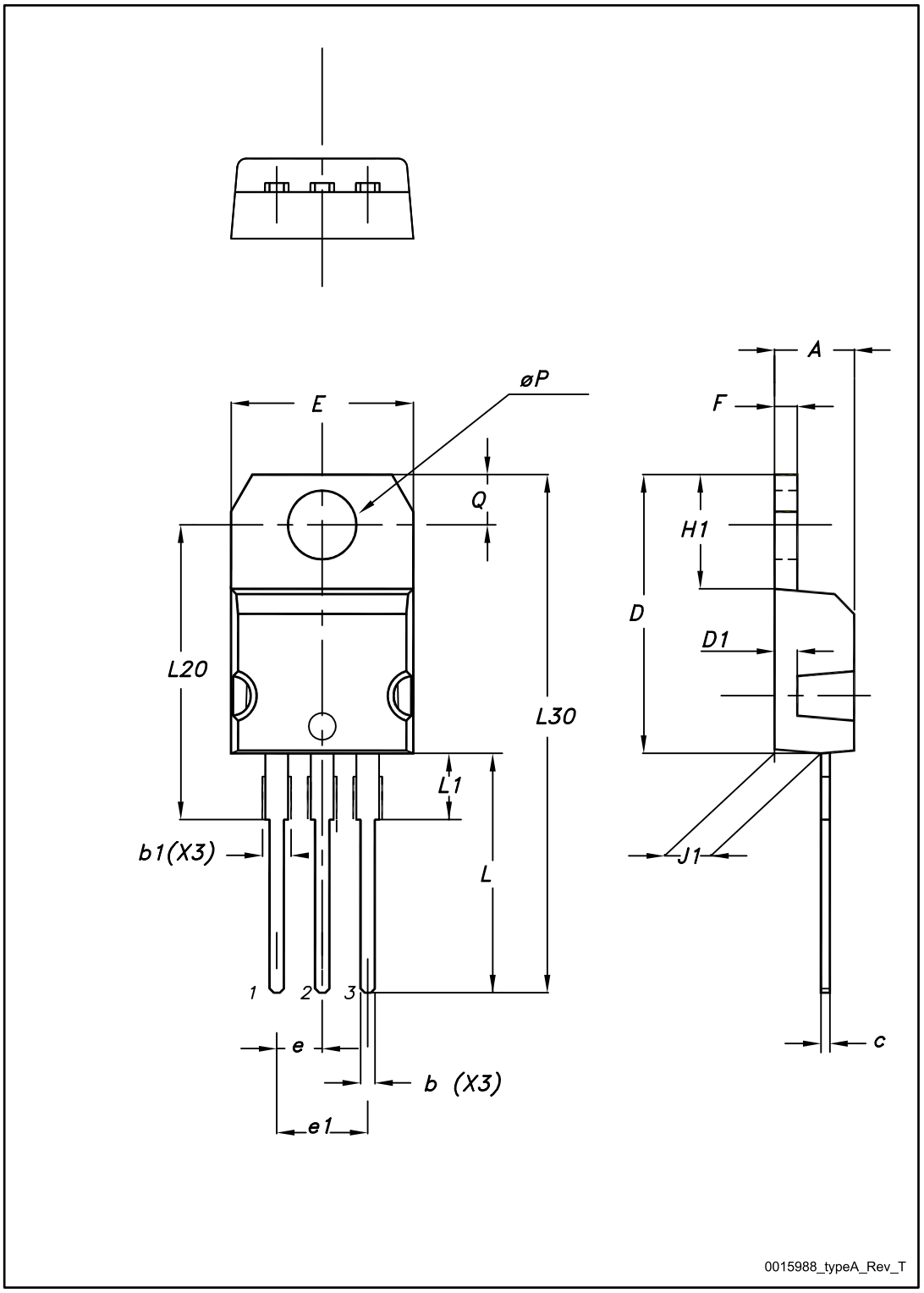


Table 10: TO-220 type A mechanical data

Dim.	mm		
	Min.	Typ.	Max.
A	4.40		4.60
b	0.61		0.88
b1	1.14		1.70
c	0.48		0.70
D	15.25		15.75
D1		1.27	
E	10		10.40
e	2.40		2.70
e1	4.95		5.15
F	1.23		1.32
H1	6.20		6.60
J1	2.40		2.72
L	13		14
L1	3.50		3.93
L20		16.40	
L30		28.90	
øP	3.75		3.85
Q	2.65		2.95

4.3 TO-247 package information

Figure 26: TO-247 package outline

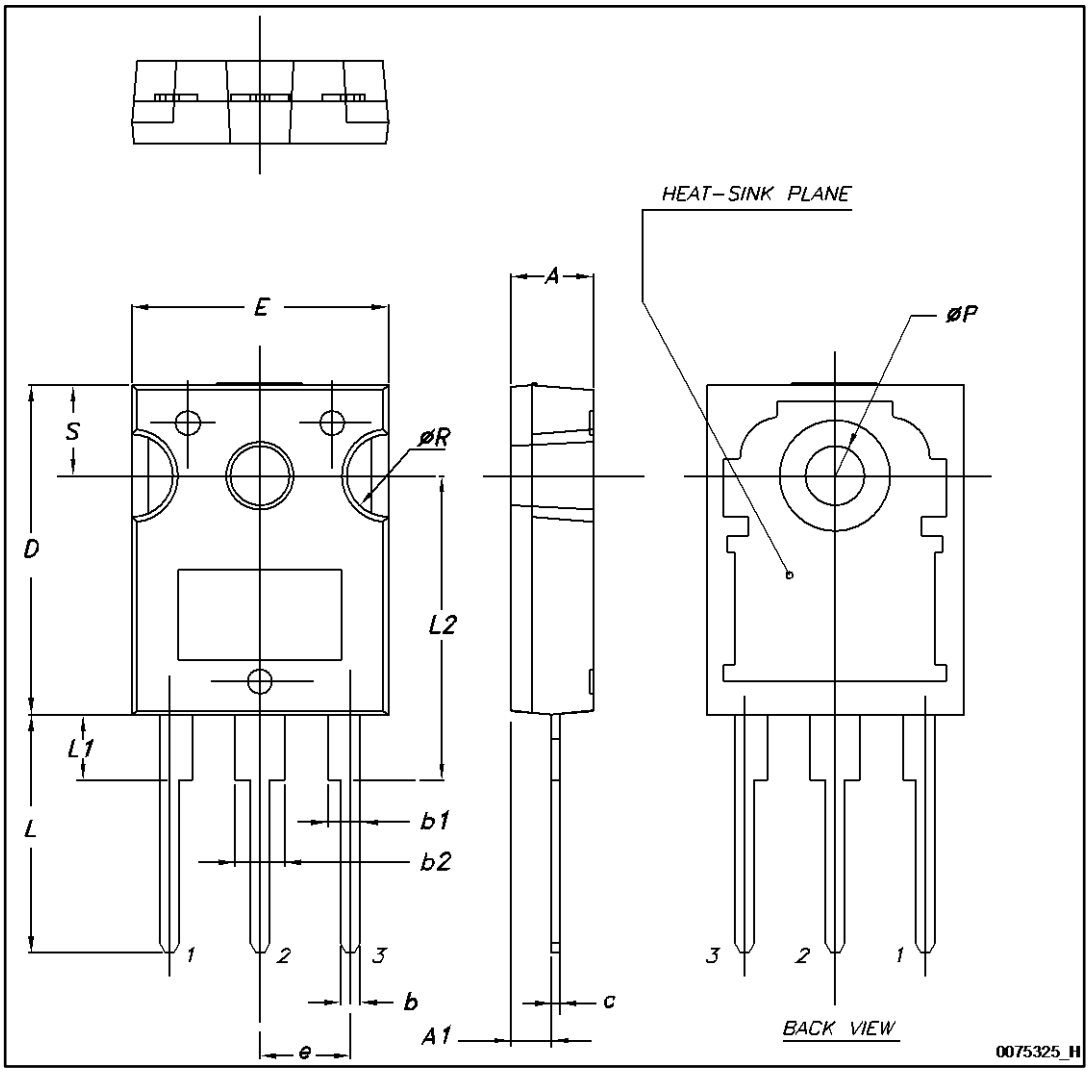


Table 11: TO-247 mechanical data

Dim.	mm.		
	Min.	Typ.	Max.
A	4.85		5.15
A1	2.20		2.60
b	1.0		1.40
b1	2.0		2.40
b2	3.0		3.40
c	0.40		0.80
D	19.85		20.15
E	15.45		15.75
e	5.30	5.45	5.60
L	14.20		14.80
L1	3.70		4.30
L2		18.50	
ØP	3.55		3.65
ØR	4.50		5.50
S	5.30	5.50	5.70

4.4 TO-247 long leads package information

Figure 27: TO-247 long leads package outline

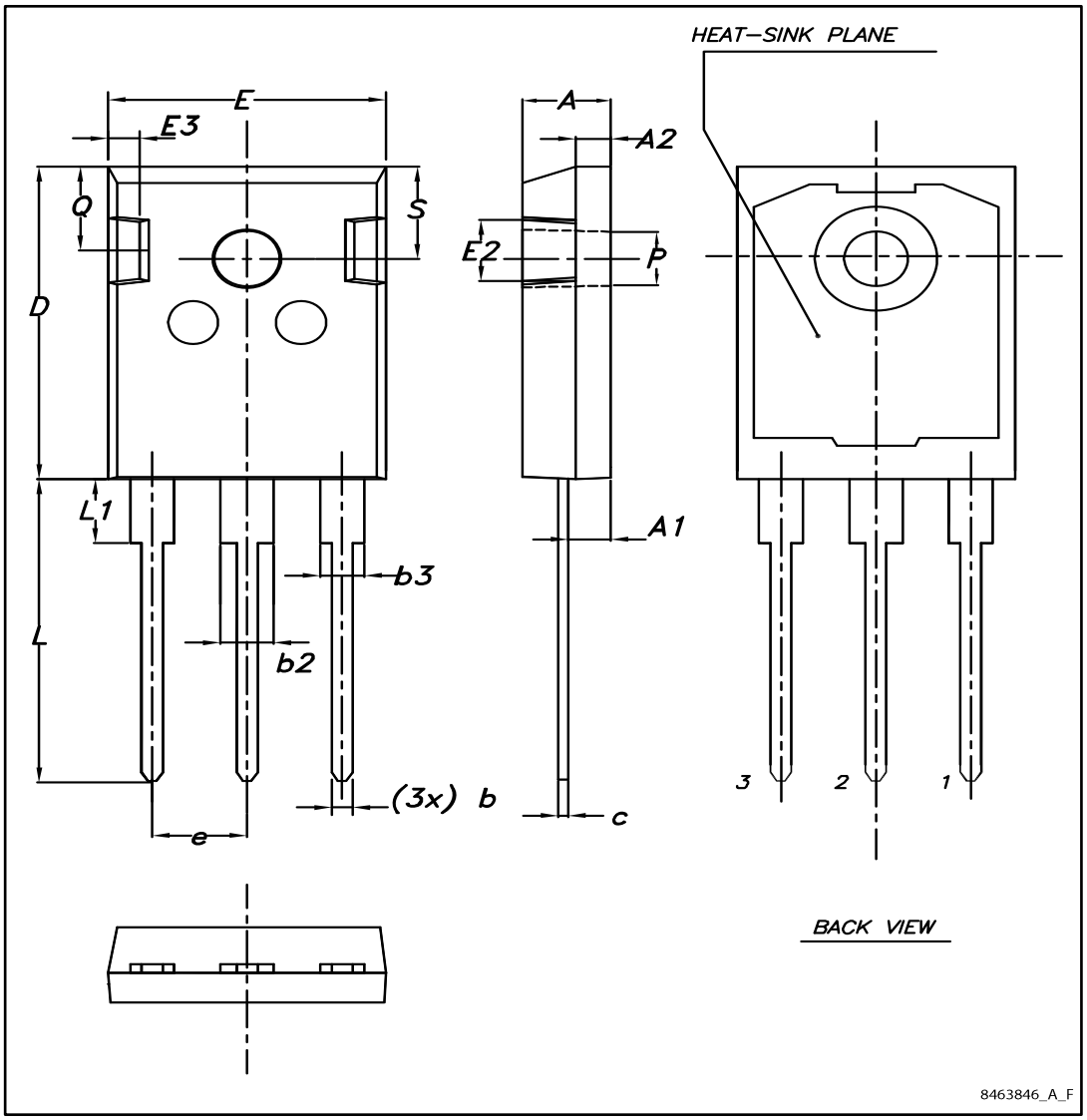


Table 12: TO-247 long leads mechanical data

Dim.	mm.		
	Min.	Typ.	Max.
A	4.90	5.00	5.10
A1	2.31	2.41	2.51
A2	1.90	2.00	2.10
b	1.16		1.26
b2			3.25
b3			2.25
c	0.59		0.66
D	20.90	21.00	21.10
E	15.70	15.80	15.90
E2	4.90	5.00	5.10
E3	2.40	2.50	2.60
e	5.34	5.44	5.54
L	19.80	19.92	20.10
L1			4.30
P	3.50	3.60	3.70
Q	5.60		6.00
S	6.05	6.15	6.25

5 Revision history

Table 13: Document revision history

Date	Revision	Changes
23-Aug-2011	1	First release.
17-Jan-2013	2	• Minor text changes • Added: H^2PAK package • The part number STB12N120K5 has been moved to a separate datasheet • Updated: • Updated: mechanical data for TO-247 package
16-May-2014	3	• The part numbers STFW12N120K5 has been moved to a separate datasheet • Added: TO-247 long leads package • Modified: I_{AR}, E_{AS}, dv/dt values in *Table 2: "Absolute maximum ratings"* • Modified: the entire typical values in *Table 5: "Dynamic"*, *Table 6: "Switching times"* and *Table 7: "Source drain diode"* • Added: *Section 2.1: "Electrical characteristics (curves)"* • Minor text changes
08-Apr-2015	4	Updated title, silhouette and description in cover page. Updated *Table 4: "On/off states"*, *Table 5: "Dynamic"*, *Figure 9: "Static drain-source on-resistance"* and *Figure 10: "Capacitance variations"*. Minor text change.

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